



# STPS16H100CT/CG/CFP/CR

## HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

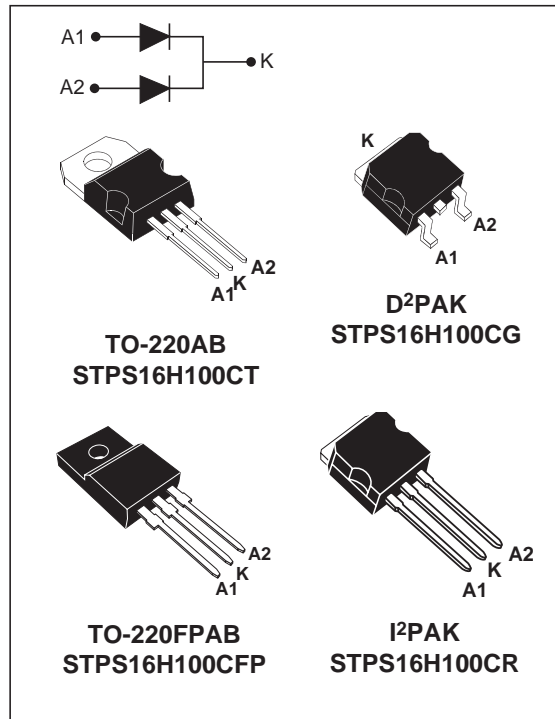
$I_{F(AV)}$	2 x 8 A
$V_{RRM}$	100 V
$T_j$ (max)	175 °C
$V_F$ (max)	0.64 V

### FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- HIGH JUNCTION TEMPERATURE CAPABILITY
- LOW LEAKAGE CURRENT
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

Dual center tap Schottky rectifier designed for high frequency miniature Switch Mode Power Supplies such as adaptators and on board DC/DC converters.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage			100	V
$I_{F(RMS)}$	RMS forward current			30	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220AB D <sup>2</sup> PAK / I <sup>2</sup> PAK	$T_c = 165^\circ\text{C}$ Per diode	8	A
		TO-220FPAB	$T_c = 150^\circ\text{C}$ Per device	16	
$I_{FSM}$	Surge non repetitive forward current		$t_p = 10$ ms sinusoidal	200	A
$I_{RRM}$	Repetitive peak reverse current		$t_p = 2$ $\mu\text{s}$ square F = 1kHz	1	A
$I_{RSM}$	Non repetitive peak reverse current		$t_p = 100$ $\mu\text{s}$ square	2	A
$P_{ARM}$	Repetitive peak avalanche power		$t_p = 1$ $\mu\text{s}$ $T_j = 25^\circ\text{C}$	8700	W
$T_{stg}$	Storage temperature range			-65 to +175	°C
$T_j$	Maximum operating junction temperature *			175	°C
$dV/dt$	Critical rate of rise of reverse voltage			10000	V/ $\mu\text{s}$

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$  thermal runaway condition for a diode on its own heatsink

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## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit	
$R_{th(j-c)}$	Junction to ambient	TO-220AB / D <sup>2</sup> PAK / I <sup>2</sup> PAK	Per diode	1.6	°C/W
		TO-220FPAB		4	
		TO-220AB / D <sup>2</sup> PAK / I <sup>2</sup> PAK	Total	1.1	°C/W
		TO-220FPAB		3.5	
$R_{th(c)}$		TO-220AB / D <sup>2</sup> PAK / I <sup>2</sup> PAK	Coupling	0.6	°C/W
		TO-220FPAB		3	

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

## STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage Current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			3.6	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$			1.6	5	mA
$V_F^{**}$	Forward Voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8\text{ A}$			0.77	V
		$T_j = 125^\circ\text{C}$	$I_F = 8\text{ A}$		0.59	0.64	
		$T_j = 25^\circ\text{C}$	$I_F = 16\text{ A}$			0.88	
		$T_j = 125^\circ\text{C}$	$I_F = 16\text{ A}$		0.67	0.73	

Pulse test : \*  $t_p = 5\text{ ms}$ ,  $\delta < 2\%$   
 \*\*  $t_p = 380\text{ }\mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation :  
 $P = 0.55 \times I_{F(AV)} + 0.011 \times I_{F(RMS)}^2$

Fig. 1: Conduction losses versus average current.

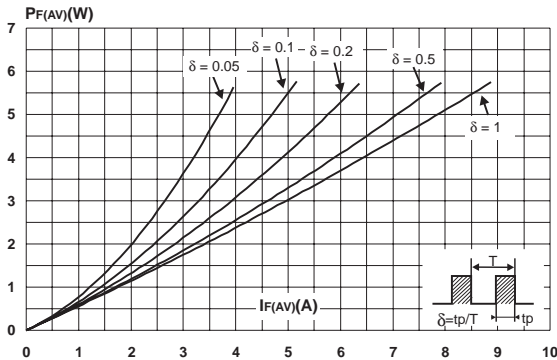
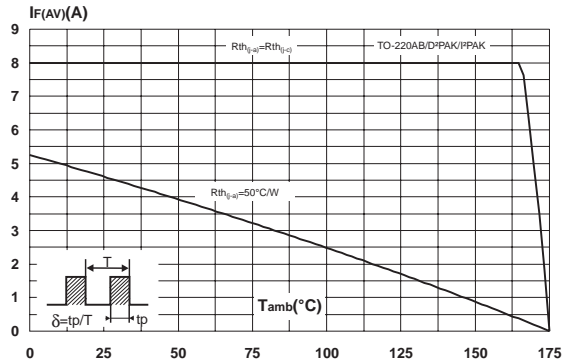
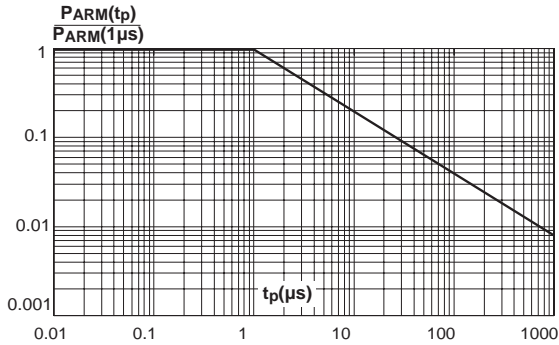


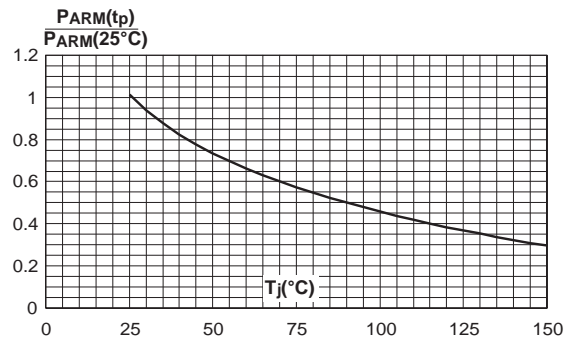
Fig. 2: Average forward current versus ambient temperature ( $\delta=0.5$ ).



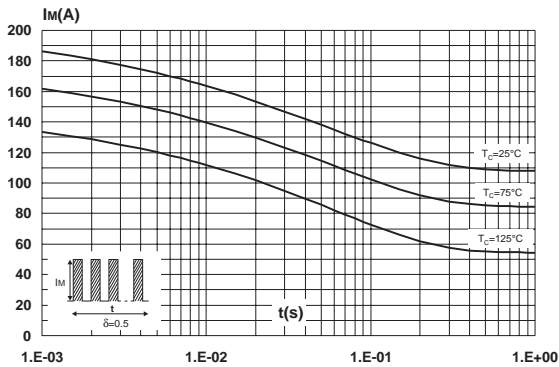
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



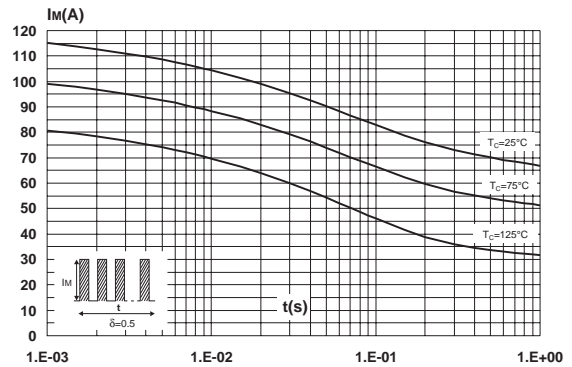
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



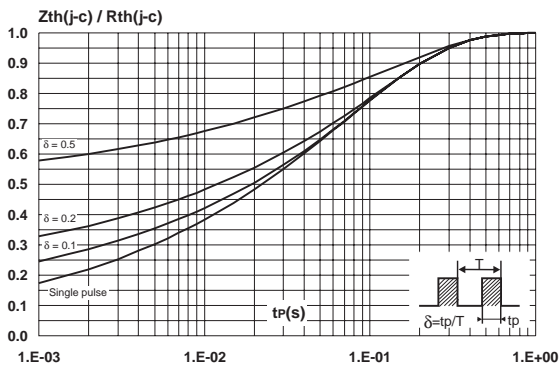
**Fig. 5-1:** Non repetitive surge peak forward current versus overload duration (maximum values) (TO-220AB, D<sup>2</sup>PAK, I<sup>2</sup>PAK).



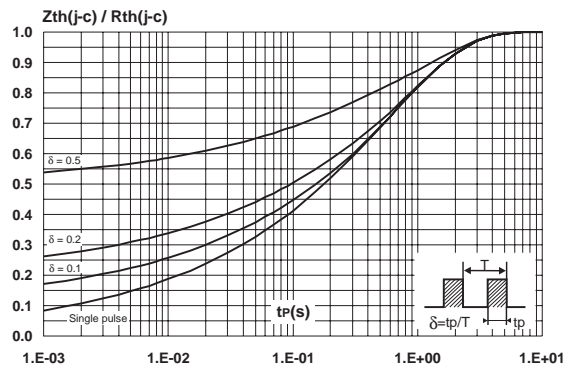
**Fig. 5-2:** Non repetitive surge peak forward current versus overload duration (maximum values) (TO-220FPAB).



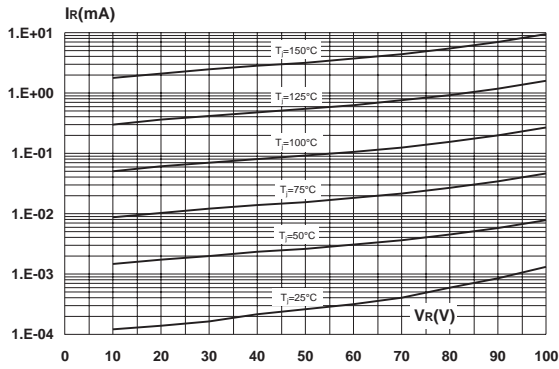
**Fig. 6-1:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB, D<sup>2</sup>PAK & I<sup>2</sup>PAK).



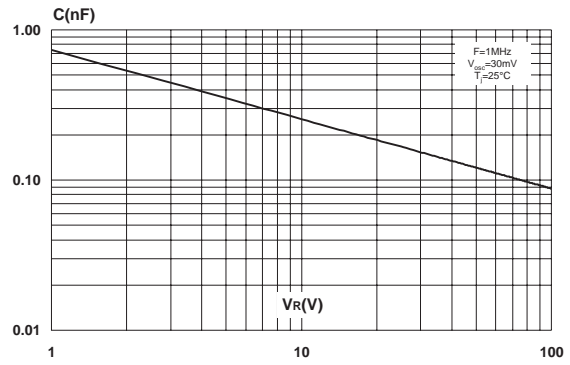
**Fig. 6-2:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB).



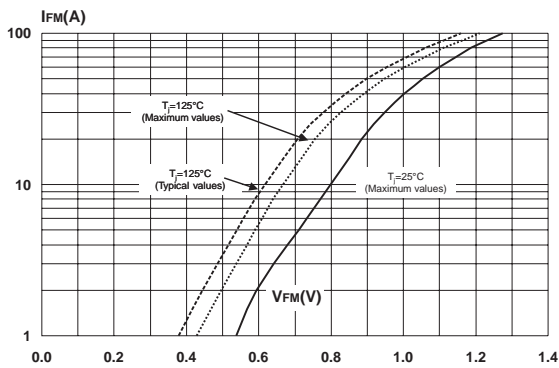
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values).



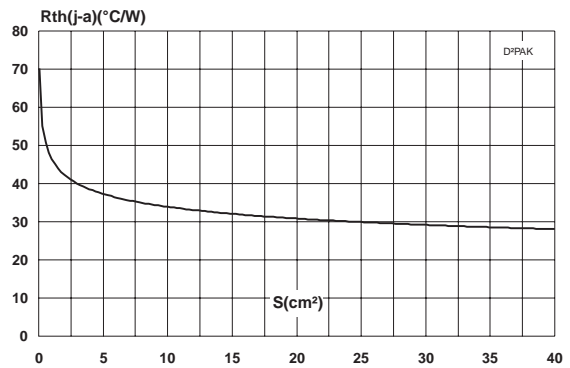
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values).



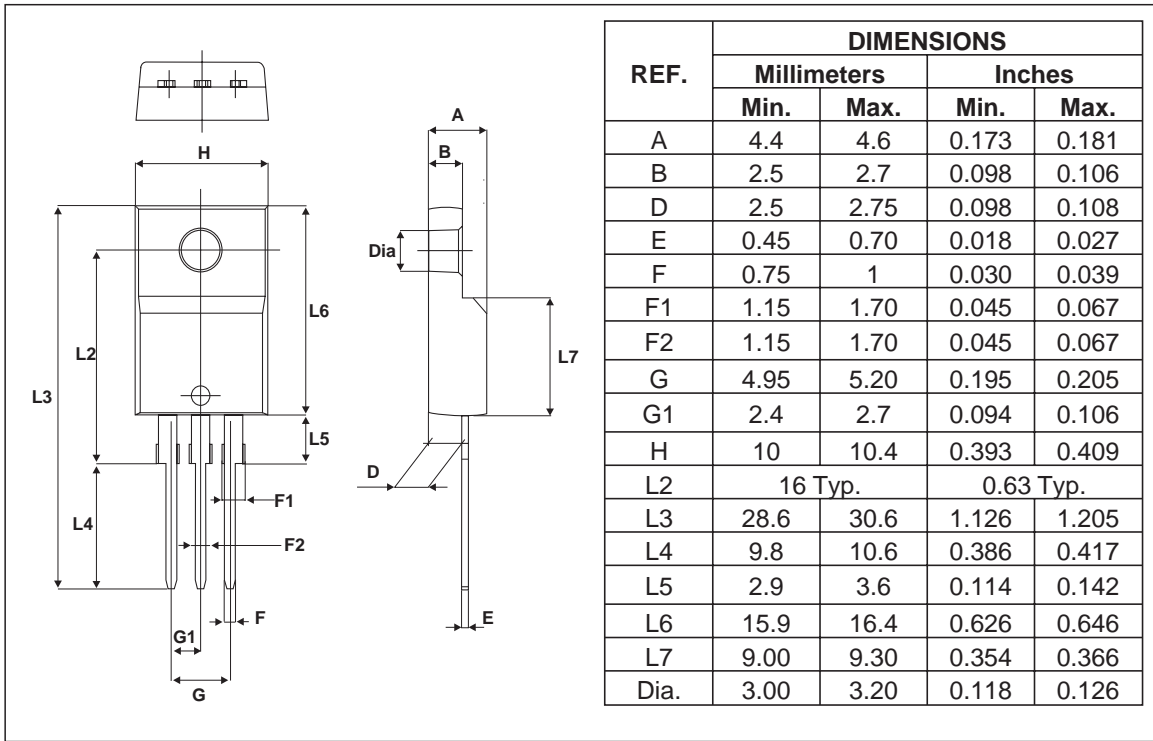
**Fig. 9:** Forward voltage drop versus forward current.



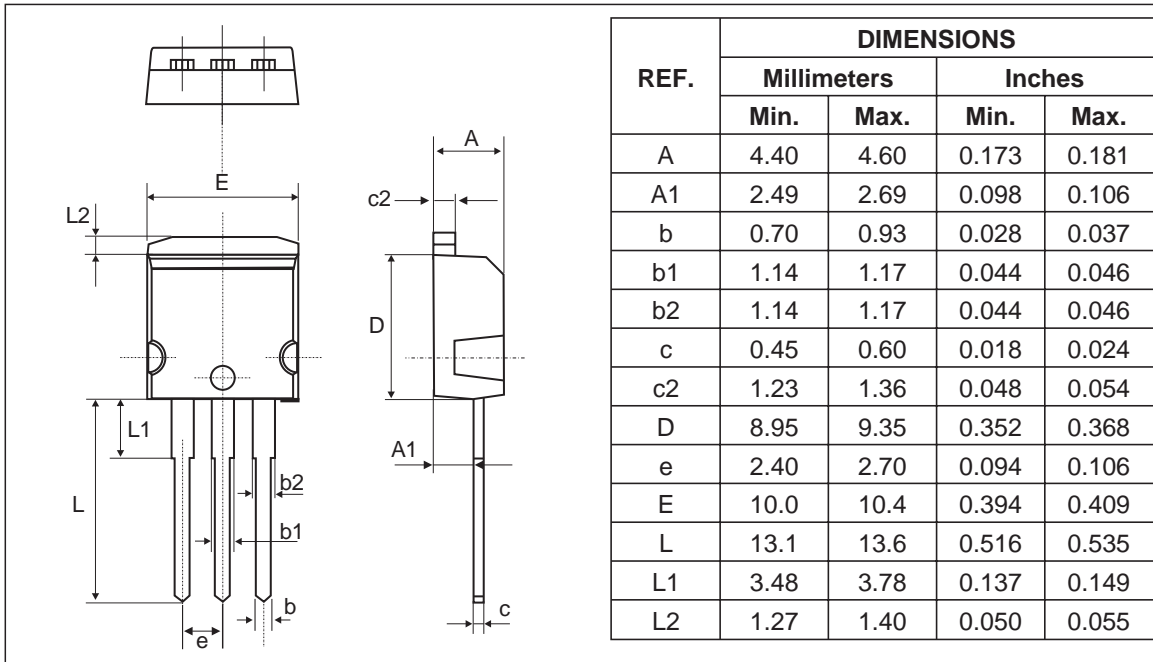
**Fig. 10:** Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu = 35 $\mu\text{m}$ ).



**PACKAGE MECHANICAL DATA**  
TO-220FPAB

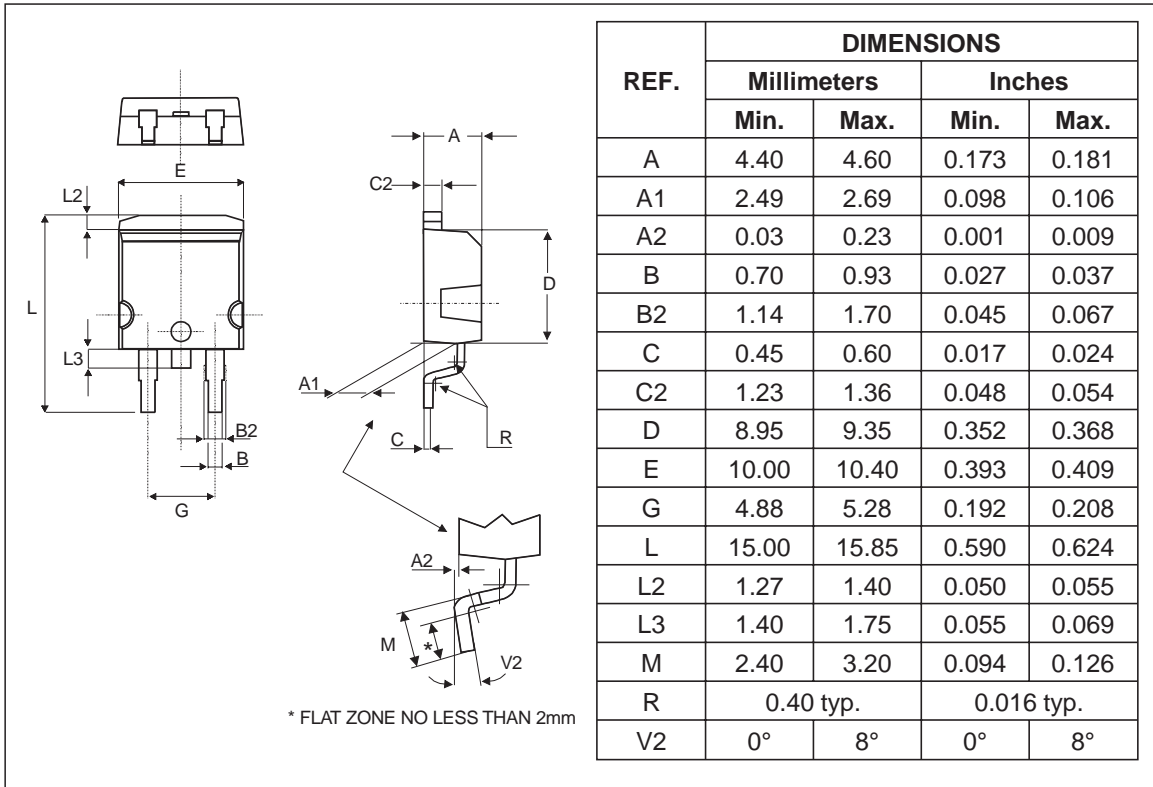


**PACKAGE MECHANICAL DATA**  
I<sup>2</sup>PAK

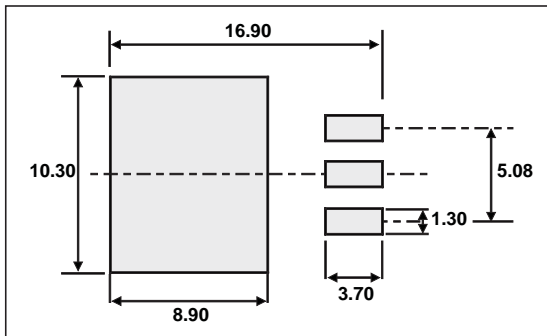


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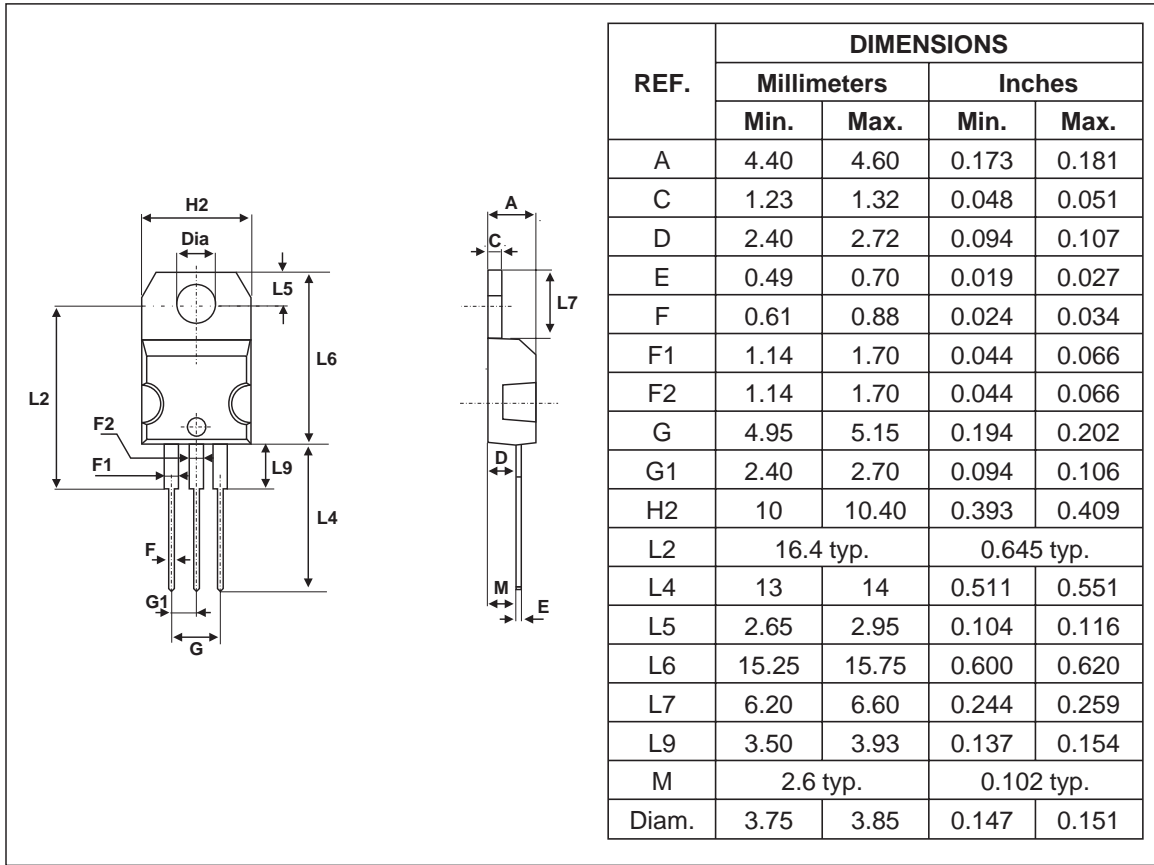
## PACKAGE MECHANICAL DATA D<sup>2</sup>PAK



## FOOTPRINT



**PACKAGE MECHANICAL DATA**  
TO-220AB



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS16H100CT	STPS16H100CT	TO-220AB	2.20 g	50	Tube
STPS16H100CFP	STPS16H100CFP	TO-220FPAB	2.0 g	50	Tube
STPS16H100CG	STPS16H100CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STPS16H100CG-TR	STPS16H100CG	D <sup>2</sup> PAK	1.48 g	1000	Tape & reel
STPS16H100CR	STPS16H100CR	I <sup>2</sup> PAK	1.9 g	50	Tube

■ EPOXY MEETS UL94,V0

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